

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the above-referenced application.

Listing of Claims:

Claims 1 - 12 (Cancelled)

13. (New) An electrostatic discharge device, comprising:

a semiconductor substrate of a first conduction type;

first and second wells of a second conduction type opposite to said first conduction type, each of said first and second wells including a first diffusion region of said first conduction type and a second diffusion region of said second conduction type, said second diffusion region in said first well being connected to said first diffusion region in said second well; and

a third well of said first conduction type located between said first well and said second well, wherein said first, second and third wells cooperate with one another to perform a bipolar action.

14. (New) The electrostatic discharge device according to claim 13, further comprising:

a fourth well of said second conduction type including a first diffusion region of said first conduction type and a second diffusion region of said second conduction type, said first diffusion region in said fourth well being connected to said second diffusion region in said second well;
and

a fifth well of said first conduction type located between said second well and said fourth well, wherein a voltage applied to said first diffusion region of said first well is higher than a voltage applied to said second diffusion region of said fourth well, and wherein said fifth well is free from a diffusion region of said first conductive type therein.

15. (New) The electrostatic discharge device according to claim 14, wherein said second, fourth and fifth well cooperate with one another to perform a bipolar action.

16. (New) The electrostatic discharge device according to claim 13, wherein said third well includes a diffusion region of said first conduction type.

17. (New) The electrostatic discharge device according to claim 16, wherein said diffusion region in said third well is exposed in a surface of said semiconductor substrate.

18. (New) The electrostatic discharge device according to claim 17, wherein said diffusion region in said third well is divided into a plurality of portions, each of said portions being apart from each other.

19. (New) The electrostatic discharge device according to claim 18, wherein said first and second wells are separated from said third well by shallow trench isolation.

20. (New) An electrostatic discharge device, comprising:

a semiconductor substrate of a first conduction type;

first and second wells of a second conduction type opposite to said first conduction type, each of said first and second wells including a first diffusion region of said first conduction type and a second diffusion region of said second conduction type, said second diffusion region in said first well being connected to said first diffusion region in said second well; and

a third well of said first conduction type disposed between said first well and said second well and including a diffusion region of said first conduction type, wherein said diffusion region in said third well being exposed in a surface of said semiconductor substrate.

21. (New) The electrostatic discharge device according to claim 20, wherein said diffusion region in said third well is divided into a plurality of portions, each of said portions being apart from each other.

22. (New) The electrostatic discharge device according to claim 20, wherein said first, second and third wells cooperate with one another to perform a bipolar action.

23. (New) The electrostatic discharge device according to claim 20, further comprising:

a fourth well of said second conduction type including a first diffusion region of said first conduction type and a second diffusion region of said second conduction type, said first diffusion region in said fourth well being connected to said second diffusion region in said second well;
and

a fifth well of said first conduction type located between said second well and said fourth well, wherein a voltage applied to said first diffusion region of said first well is higher than a voltage applied to said second diffusion region of said fourth well, and wherein said fifth well is free from a diffusion region of said first conductive type therein.

24. (New) The electrostatic discharge device according to claim 23, wherein said second, fourth and fifth well cooperate with one another to perform a bipolar action.

25. (New) The electrostatic discharge device according to claim 20, wherein said first and second wells are separated from said third well by shallow trench isolation.

26. (New) An electrostatic discharge device, comprising:

a semiconductor substrate of a first conduction type;

first and second wells of a second conduction type opposite to said first conduction type, each of said first and second wells including a first diffusion region of said first conduction type and a second diffusion region of said second conduction type, said second diffusion region in said first well being connected to said first diffusion region in said second well; and

a third well of said first conduction type formed between said first well and said second well and including a diffusion region of said first conduction type, wherein said diffusion region in said third well is divided into a plurality of portions, each of said portions being apart from each other.

27. (New) The electrostatic discharge device according to claim 26, wherein said diffusion region in said third well is exposed in a surface of said semiconductor substrate.

28. (New) The electrostatic discharge device according to claim 26, wherein said first, second and third wells cooperate with one another to perform a bipolar action.

29. (New) The electrostatic discharge device according to claim 26, further comprising:

a fourth well of said second conduction type including a first diffusion region of said first conduction type and a second diffusion region of said second conduction type, said first diffusion region in said fourth well being connected to said second diffusion region in said second well;
and

a fifth well of said first conduction type located between said second well and said fourth well, wherein a voltage applied to said first diffusion region of said first well is higher than a voltage applied to said second diffusion region of said fourth well, and wherein said fifth well is free from a diffusion region of said first conductive type therein.

30. (New) The electrostatic discharge device according to claim 29, wherein said second, fourth and fifth well cooperate with one another to perform a bipolar action.

31. (New) The electrostatic discharge device according to claim 26, wherein said first and second wells are separated from said third well by shallow trench isolation.